

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently amended) A method of manufacturing circuit devices, comprising:
preparing a laminated plate by laminating a thin first conductive film and a thick second conductive film via a third conductive film;
forming a fine conductive pattern layer by etching said first conductive film into a ~~desirable~~ pattern;
removing the third conductive film by use of said conductive pattern layer as a mask and thus forming anchor portions where said third conductive film is depressed further inside than said conductive pattern layer;
fixedly fitting semiconductor elements on said conductive pattern layer via an insulating adhesive layer and partially filling said insulating adhesive layer into said anchor portions;
electrically connecting electrodes of said semiconductor elements with ~~predetermined~~ parts of said conductive pattern layer;
covering said semiconductor elements with a sealing resin layer and filling said sealing resin layer into said anchor portions; and
exposing said sealing resin layer and said third conductive film on the rear surface by removing said second conductive film.
2. (Original) The method of Claim 1, wherein said third conductive film is used as an etching stopper when the first conductive film is etched.
3. (Original) The method of Claim 2, wherein a solution containing ferric chloride or cupric chloride is used as a solution to perform said etching.

4. (Original) The method of Claim 1, wherein said anchor portions are formed by overetching said third conductive film by use of said conductive pattern layer or a resist for forming said conductive pattern as a mask.

5. (Original) The method of Claim 4, wherein said etching solution is an iodine-based solution.

6. (Original) The method of Claim 1, wherein said third conductive film is peeled off by electrolysis by use of said conductive pattern layer or a resist for forming said conductive pattern as a mask, and said anchor portions are formed by over-peeling.

7. (Currently amended) The method of Claim 1, wherein said third conductive film and said sealing resin layer in said anchor portions, which remain ~~remaining~~ after entirely etching the second conductive film, are exposed.

8. (Original) The method of Claim 7, wherein external electrodes are formed by adhering a brazing filler material to the remaining third conductive film.

9. (Currently amended) ~~A method of manufacturing circuit devices, comprising:~~
~~preparing a laminated plate by laminating a thin first conductive film and a thick second~~
~~conductive film via a third conductive film;~~

The method of claim 1 including:

selectively forming pads formed of a fourth conductive film on said first conductive film;
and

~~forming a fine conductive pattern layer by etching said first conductive film into a~~
~~desirable pattern;~~

~~removing said third conductive film by use of the conductive pattern layer as a mask and~~
~~thus forming anchor portions where said third conductive film is depressed further inside than~~
~~said conductive pattern layer;~~

~~fixedly fitting semiconductor elements on said conductive pattern layer via an insulating~~
~~adhesive layer and filling said insulating adhesive layer into said anchor portions;~~

electrically connecting the electrodes of said semiconductor elements with said pads on
~~predetermined parts of said conductive pattern layer;~~

~~covering said semiconductor elements with a sealing resin layer and filling said sealing~~
~~resin layer into the anchor portions; and~~

~~exposing said sealing resin layer and third conductive film on the rear surface by~~
~~removing said second conductive film.~~

10. (Original) The method of Claim 9, wherein said third conductive film is used as an
etching stopper when the first conductive film is etched.

11. (Original) The method of Claim 10, wherein a solution containing ferric chloride or
cupric chloride is used as a solution to perform said etching.

12. (Original) The method of Claim 9, wherein said anchor portions are formed by over-etching said third conductive film by use of said conductive pattern layer or a resist for forming said conductive pattern as a mask.

13. (Original) The method of Claim 12, wherein said etching solution is an iodine-based solution.

14. (Original) The method of Claim 9, wherein said third conductive film is peeled off by electrolysis by use of said conductive pattern layer or a resist for forming said conductive pattern as a mask, and said anchor portions are formed by over-peeling.

15. (Currently amended) The method of Claim 9, wherein said third conductive film and said sealing resin layer in said anchor portions, which remain ~~remaining~~ after entirely etching the second conductive film, are exposed.

16. (Original) The method of Claim 15, wherein external electrodes are formed by adhering a brazing filler material to the remaining third conductive film.

17. (New) A method of manufacturing a support on which to mount semiconductor elements, the method comprising:

providing a laminated plate in which a first conductive film and a thicker second conductive film are laminated via a third conductive film;

etching the first conductive film to form a fine conductive pattern layer; and

removing the third conductive film while using the conductive pattern layer as a mask to form anchor portions, wherein the third conductive film is depressed further inside than the conductive pattern layer.

18. (New) The method of Claim 17, wherein said third conductive film is used as an etching stopper when the first conductive film is etched.

19. (New) The method of Claim 18, wherein a solution containing ferric chloride or cupric chloride is used as a solution to perform said etching.

20. (New) The method of Claim 17, wherein said anchor portions are formed by over-etching said third conductive film by use of said conductive pattern layer or a resist for forming said conductive pattern as a mask.

21. (New) The method of Claim 20, wherein said etching solution is an iodine-based solution.

22. (New) The method of Claim 17, wherein said third conductive film is peeled off by electrolysis by use of said conductive pattern layer or a resist for forming said conductive pattern as a mask, and said anchor portions are formed by over-peeling.

23. (New) The method of Claim 17, wherein said third conductive film and said sealing resin layer in said anchor portions, which remain after entirely etching the second conductive film, are exposed.

24. (New) The method of Claim 23, wherein external electrodes are formed by adhering a brazing filler material to the remaining third conductive film.

25. (New) A method of manufacturing circuit devices using a substrate comprising a thick conductive film that supports a fine conductive pattern layer on a conductive film pattern, wherein portions of the fine conductive pattern layer extend beyond corresponding portions of the conductive film pattern to form anchor portions between adjacent portions of the conductive film pattern, the method comprising;

mounting semiconductor elements on said conductive pattern layer of said substrate via an insulating adhesive layer, wherein the insulating adhesive layer partially fills the anchor portions;

electrically connecting electrodes of the semiconductor elements with portions of said conductive pattern layer;

covering the semiconductor elements with a sealing resin layer and filling remaining sections of the anchor portions with the sealing resin layer; and

removing said thick conductive film to expose rear surfaces of the sealing resin layer and said conductive film pattern.